Evolution of phase purity and texture on annealing of BiFeO_3 thin film prepared by sol-gel technique

Priyadarshini Dash^{1*}, B N Dash², Haripriya Rath¹, Chandana Rath³ and N C Mishra¹

¹Department of Physics, Utkal University, Bhubaneswar-751 004, Orissa, India

²Department of Physics, SVM College, Jagatsinghpur-754 103, Orissa, India

³School of Material Science & Technology, Institute of Technology, Banaras Hindu University, Varanasi 221 005, Uttar Pradesh, India

E-mail: lipundashl6@yahoo.com

Abstract : We report preparation of phase pure BiFeO_3 thin films on glass, ITO and Si(100) substrates through chemical route using spin coating technique. Sol-gel process was adopted to prepare the films using bismuth nitrate and iron nitrate as precursors. X-Ray diffraction and Raman spectroscopy studies revealed amorphous nature of the as deposited films. Rhombohedral crystalline phase of BiFeO_3 evolved on annealing the films at 500°C, but with $\text{Bi}_2\text{Fe}_4\text{O}_9$ and $\text{Bi}_{24}\text{Fe}_2\text{O}_{39}$ as impurity phases. Increasing the annealing temperature to 550°C caused a drastic reduction of the impurity phases and at 600°C, the films were phase-pure BiFeO_3 . Micro Raman spectra showed features consistent with the reported characteristic peaks of BiFeO_3 crystalline phase for films annealed at 500 and 550°C. Crystallite size obtained from X-ray diffraction line width analysis are within 30 to 40 nm. Atomic force microscopy (AFM) however showed grain size of ~192 nm, indicating polycrystalline nature of the grains.

Keywords : Thin film, bismuth ferrite, multiferroic.

PACS Nos. : 68.55.Nq, 68.55.a, 81.15.-z

1. Introduction

Multiferroic materials have attracted extensive attention due to their potential usage in information technology, data-storage media, spintronics and sensors [1–3]. In multiferroics, one can control the various order parameters like magnetization, polarization and strain by their corresponding driving forces like magnetic field, electric field and stress. In addition, one can also control polarization by magnetic field and stress, magnetization by electric field and stress and strain by both electric and magnetic fields, thus exemplifying the properties like piezoelectric, magneto-strictive and magneto-electrics [4].

Bismuth ferrite, BiFeO_3 (BFO) is a multiferroic material, which has gained

*Corresponding Author

importance due its stable ferroelectric and antiferromagnetic coupling at room temperature, and due to the fact that its ferroelectric properties are very much enhanced in thin film form [5–7]. The associated mechanism correlating the system geometry with magneto electric response is still not clear. On the experimental front, synthesis of phase pure BiFeO_3 has posed several difficulties. BiFeO_3 belongs to the rhombohedral system with space group $R\bar{3}m$ and $a = 0.396$ nm, $\alpha = 89.5$ [8,9]. It is ferroelectric with a high Curie temperature of 850°C and a high Neel temperature of about 397°C . The antiferromagnetic state has a canted spin structure resulting in a net spontaneous magnetization [10].

In recent years, the sol-gel technique has emerged as a versatile method for synthesizing different inorganic materials. Apart from the advantage of low temperature processing a sol-gel route makes it possible to obtain nano-particle materials [10]. Several attempts therefore have been taken to prepare BFO phase using sol-gel method. The task becomes difficult because of the narrow temperature range in which BFO stabilizes and there are a number of other phases of Bi and Fe, which appear if temperature is not controlled accurately. During synthesis, the kinetics of formation always leads to a mixture of BFO as a major phase along with other impurity phases [11,12]. The problem becomes still more complex when BFO is prepared in thin film form. It has therefore become a challenge for materials scientists to prepare phase pure BFO over the years [13].

In this work, sol-gel method is used to grow bismuth ferrite films on glass, ITO/glass and Si(100) substrates. Phase formation and microstructure of the films at different annealing temperature was studied using glancing angle X-ray diffractometer (GAXRD), micro-Raman spectroscopy and atomic force microscopy (AFM). We show that films annealed at 600°C yield phase pure BFO phase with randomly oriented grains and the grains are polycrystalline in nature.

2. Experimental details

BFO thin films were prepared by a sol-gel process [14] using bismuth nitrate $[\text{Bi}(\text{NO}_3)_3 \cdot 5\text{H}_2\text{O}]$ (Merck) and iron nitrate $[\text{Fe}(\text{NO}_3)_3 \cdot 9\text{H}_2\text{O}]$ (Merck) as starting materials. Bismuth nitrate and iron nitrate were mixed with a mole ratio of 1 : 1 and dissolved at room temperature in 2-methoxyethanol and stirred for 30 min. Then acetic anhydride was added to dehydrate and ethanolamine was added to adjust the viscosity under constant stirring. The concentration of the stock solution was adjusted to 0.3 M by adding 2-methoxyethanol. The above process was performed in an ambient atmosphere at room temperature.

Films from the above stock solution were deposited on glass, Si(100) wafers and indium tin oxide (ITO) coated glass substrates. The substrates were cleaned thoroughly by ultrasonication in alcohol and acetone. The depositions were carried out by spin coating using Apex Instruments make spin coater (model-SCU 2004) at 5500 rpm for

15 seconds. Each deposition layer was pre-annealed at 350°C for 3 min in a tubular furnace. The spin coating was repeated 16 times to obtain BFO films of adequate thickness. In order to get perovskite phase, the films were annealed at 500, 550 and 600°C for 1 h.

Structural and microstructural analysis of the films were done by X-ray diffraction using Bruker-D8 Advance model glancing angle X-ray diffractometer with Cu K α radiation ($\lambda_{K\alpha} = 1.54439 \text{ \AA}$) at a step of 2°/min in the range of $2\theta = 20^\circ\text{--}60^\circ$. Micro-Raman spectra were recorded in backscattering geometry at ambient conditions by charge coupled device collection using Renishaw-INVIA Micro-Raman Spectroscopy System with 514 nm excitation lines from Ar⁺ laser. Grain size of the annealed films was determined by atomic force microscopy (AFM).

3. Results and discussion

The XRD patterns of the BFO thin films deposited on different substrates and annealed at different temperatures are shown in Figure 1. The as deposited film did not show

Figure 1. XRD patterns of as deposited and 500, 550, 600°C annealed BiFeO₃ thin films.

any peak of any of the phases of bismuth iron oxide as reported in JCPDS file. The film was thus amorphous. Crystallinity evolved after annealing the films at 500°C and above as seen from GAXRD. The peaks match with the reported rhombohedral structure of BFO quite well and XRD shows polycrystalline nature of the films [13,14]. The XRD pattern of the films annealed at 500°C are mainly composed of peaks due to rhombohedral BFO phase. There are however a few peaks occurring in a 2θ interval of 27° to 31° , which could not be assigned to BFO phase. A comparison of these peaks with those reported in JCPDS file indicated that impurity phase like Bi₂Fe₄O₉ and Bi₂₄Fe₂O₃₉ form in the 500°C annealed sample. Because of the kinetics of formation,

a mixture of BFO as a major phase along with other impurity phases is always obtained during synthesis. The impurity phases like $\text{Bi}_2\text{Fe}_4\text{O}_9$ [11] and $\text{Bi}_{46}\text{Fe}_2\text{O}_{72}$ [12,14] along with the main phase BFO have been reported in the literature. Peaks due to the impurity phases diminished with increasing the annealing temperature to 550°C. Films annealed at this temperature however show unidentified peaks at diffraction angle 37.78, 46.52 (* marked), which do not match with any phase of bismuth iron oxide as seen from JCPDS file. Film annealed at 600°C contains peaks only due to the rhombohedral BFO phase and no impurity phase was detected. Formation of a single perovskite phase at the annealing temperature of 600°C indicates that there is an optimum temperature range in which the impurity phases are suppressed and pure perovskite BFO forms.

The synthesis of pure polycrystalline BFO samples is quite subtle because it is necessary to take both kinetic and thermodynamic properties into account. Speranskaya *et al* [15], through a detailed analysis of the different phases of BFO have shown that two impurities phases ($\text{Bi}_2\text{Fe}_4\text{O}_9$ and $\text{Bi}_{25}\text{FeO}_{39}$) can form along with BFO. Indeed the high volatility of Bi_2O_3 leads to the formation of a Bi-poor phase, $\text{Bi}_2\text{Fe}_4\text{O}_9$ as observed in the present study. Along with this expected bismuth deficient impurity phase $\text{Bi}_2\text{Fe}_4\text{O}_9$, we also observe bismuth excess phase $\text{Bi}_{24}\text{Fe}_2\text{O}_{39}$, the origin of which is not clear at present. This phase, we believe is a consequence of local stoichiometry fluctuation in the sample annealed at 500°C. Many other variants of bismuth excess phases like $\text{Bi}_{46}\text{Fe}_2\text{O}_{72}$ [12,14], $\text{Bi}_{25}\text{FeO}_{40}$ [16] have also been observed. In some of these cases, a small excess of Bi_2O_3 in the reactants, necessary to compensate for the loss of Bi_2O_3 , has been shown to lead to the formation of the Bi-rich phases.

To probe into the orientation of crystallites in the films and their evolution with sintering temperature, we compare the XRD peak intensities in the present study with that reported by others in BFO films [14] and powder samples [13]. Liu *et al* observe a transition from (110) preferred orientation of the grains in 500°C annealed film to random orientation in 600°C annealed film. On the contrary, we find that the peak intensities are not only independent of the sintering temperature, but also are independent on the substrate used. The almost equal intensity of (101) and (110) peaks indicate that the grains in our case are randomly oriented as was observed in powder BFO samples [13]. This might be the consequence of sixteen coatings we have taken during thin film deposition by spin coating technique.

Crystallite size, D of the BFO was calculated from XRD data using Debye-Scherrer formula $D = 0.9\lambda/\beta_{2\theta}\cos\theta$, where λ is the wavelength of the X-ray used (1.54439 Å), $\beta_{2\theta}$ is the full width at half maximum of the diffraction peak at the angle 2θ , θ is the Bragg angle and 0.94 is the shape factor [17].

The Debye-Scherrer formula gives the average crystallite size of the samples annealed within a temperature interval of 500 to 600°C to lie within 30 to 40 nm. AFM analysis of the BFO thin film annealed at 600°C however revealed the grain size as

192 nm (Figure 2). The grains are of uniform size and seem to be self assembled to give a linearly aligned array of nanoparticles. The widely different value of the crystallite size and the grain size indicates that the grains are not single crystalline. Rather these are made up of a large number of crystallites. From the volume ratio of the grains and the crystallites, we find that the grains are made up of approximately 150 crystallites.

Figure 2. AFM image of polycrystalline BiFeO₃ thin film annealed at 600°C.

The unpolarized Raman spectra of as deposited, 500°C and 550°C annealed BFO thin films taken at room temperature are shown in Figure 3. The absence of Raman

Figure 3. Raman spectra of as deposited and 500 and 550°C annealed BiFeO₃ thin films.

spectra of the BFO for the as deposited films shows amorphous nature of the film in conformity with the XRD result. Characteristic peaks for BFO appear in the Raman spectra of thin films annealed at 500°C and 550°C. The peaks match with that reported

by Singh *et al* and Lou *et al* [18,19] and were assigned to the different Raman active modes as shown in Table 1. The small difference that we observe between the 500°C and 550°C annealed thin films may be due to the different substrates used as well as the different annealing temperatures for the growth of these films.

Table 1. Comparison of Raman frequency in the present study with that of reported values.

Raman frequency (cm ⁻¹) Present work		Reported [18]	Reported [19]	Assignment
Annealing temperature				
500°C	550°C			
140.44	–	138	141	A ₁ (LO)
171.253	168.53	168	170	A ₁ (LO)
216.639	211.48	212	215	A ₁ (LO)
260.553	260.29	–	261	–
276.352	276.09	275	276	E(TO)
348.865	338.98	335	337	E(TO)
365.69	363.03	363	368	E(TO)
–	–	425	–	A ₁ (LO)
469.446	465.63	456	467	E(TO)
–	–	549	518	E(TO)
598.695	589.12	597	604	E(TO)
819.234	818.99	–	–	–

4. Conclusion

Both glancing angle X-ray diffraction and Raman scattering studies on BFO thin films spin coated on glass, ITO/glass and Si(100) substrates revealed that the as deposited films are amorphous. The rhombohedral structure evolves with minor impurity phases on annealing the films at 500°C. Phase purity of the films improves with increasing annealing temperature from 500 to 600°C. Phase pure BFO could be obtained on annealing the films at 600°C. Comparison of the grain size with the crystallite size revealed that the grains are polycrystalline containing about 150 crystallites in them. The XRD peak intensities indicate that the grains are randomly oriented.

References

- [1] M Fiebig, T Lottermoser, D Frohlic, A V Goltsev and R V Pisarev *Nature* **419** 818 (2002)
- [2] M M Kumar, V R Palkar, K Srinivas and S V Suryanarayana *Appl. Phys. Lett.* **76** 2764 (2000)
- [3] N A Hill *J. Phys. Chem.* **B104** 6694 (2000)
- [4] A Srinivas, D W Kim, K S Hong and S V Suryanarayana *Appl. Phys. Lett.* **83** 2217 (2003)
- [5] J Wang, J B Neaton, H Zheng, V Nagarajan, S B Ogale, B Liu, D Viehland, V Vaithyanathan, D G Schlom, U V Waghmare, N A Spaldin, K M Rabe, M Wuttig and R Ramesh *Science* **299** 1719 (2003)
- [6] V R Palkar, J John and R Pinto *Appl. Phys. Lett.* **80** 1628 (2002)

- [7] J Li, J Wang, M Wuttig, R Ramesh, N Wang, B Ruetter, A P Pyatakov, A K Zvezdin and D Viehland *Appl. Phys. Lett.* **84** 5261 (2004)
- [8] A G Tutov *Fiz Tverd Tela (FTVTA)* **11** 2681 (1969)
- [9] G D Achenbach, R Gerson and W J James *J. Am. Ceram. Soc.* **50** 437 (1967)
- [10] S W Lee and C S Kim *J. Magn.* **10** 84 (2005)
- [11] C Tabares-Munoz, J P Rivera, A Monnier and H Schmid *Jpn. J. Appl. Phys. Part 1* **24** 1051 (1985)
- [12] J R Teague, R Gerson and W J James *Solid State Commun.* **8** 1073 (1970)
- [13] Deepti Kothari, V Raghavendra Reddy, Ajay Gupta, D M Phase, N Lakshmi, S K Deshpande and A M Awasthi *J. Phys. : Condens. Matter* **19** 136202 (2007)
- [14] Hongri Liu, Zuli Liu, Qing Liu and Kailun Yao *Thin Solid Films* **500** 105 (2006)
- [15] E I Speranskaya, V M Skorikov and E Ya Rode *Bull. Acad. Sci. USSR, Phys. Ser.* **30** 874 (1965)
- [16] A Maitre, M Francois and J C Gachon *Journal of Phase Equilibria and Diffusion* **Vol.25** No. 1 (2004)
- [17] B D Culity *Element of X-ray Diffraction* (MA Reading : Addison-Wesley) (1978)
- [18] M K Singh, H M Jang, S Ryu and M-Ho Jo *Appl. Phys. Lett.* **88** 042907 (2006)
- [19] X J Lou, C X Yang, T A Tang, Y Y Lin, M Zhang and J F Scott *Appl. Phys. Lett.* **90** 262908 (2007)